

NCP339

3 A Ultra-Small Controlled Load Switch with Auto-Discharge Path and Reverse Current Control

The NCP339 is a very low Ron MOSFET controlled by external logic pin, allowing optimization of battery life, and portable device autonomy.

Indeed, due to a current consumption optimization with PMOS structure, leakage currents are eliminated by isolating connected IC on the battery when not used.

Reverse blocking control is automatically engage if OUT pin voltage is higher than IN pin voltage, eliminate leakages current from OUT to IN.

Proposed in a wide input voltage range from 1.2 V to 5.5 V, in a small 1 x 1.5 mm WLCSP6, pitch 0.5 mm.

Features

- 1.2 V – 5.5 V Operating Range
- 19 mΩ P MOSFET at 4.5 V
- DC Current up to 3 A
- Soft Start Control
- Low Quiescent Current
- Reverse Blocking
- Active High EN pin
- WLCSP6 1 x 1.5 mm
- This is a Pb-Free Device

Typical Applications

- Mobile Phones
- Tablets
- Digital Cameras
- GPS
- Portable Devices
- Computers



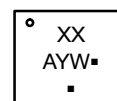
ON Semiconductor®

<http://onsemi.com>



WLCSP6, 1.00x1.50
CASE 567FH

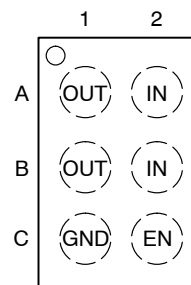
MARKING DIAGRAM



XX = NP or DP
A = Assembly Location
Y = Year
W = Work Week
▪ = Pb-Free Package

(*Note: Microdot may be in either location)

PACKAGE PINOUT DIAGRAM



(Top View)

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 9 of this data sheet.

NCP339

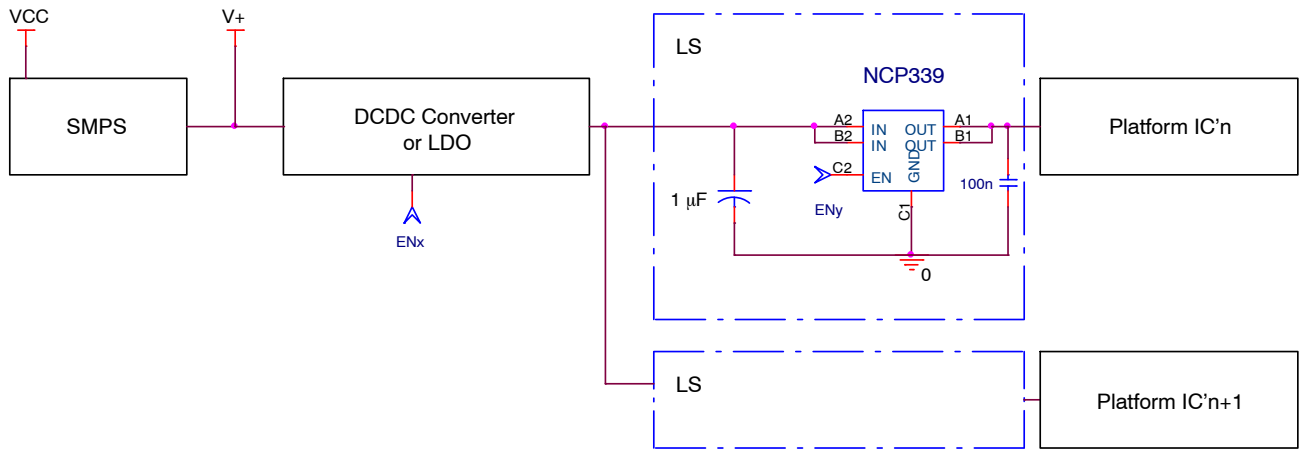


Figure 1. Typical Application Circuit

Table 1. PIN FUNCTION DESCRIPTION

Pin Name	Pin Number	Type	Description
IN	A2, B2	POWER	Load-switch input voltage; connect a 1 μ F or greater ceramic capacitor from IN to GND as close as possible to the IC.
GND	C1	POWER	Ground connection.
EN	C2	INPUT	Enable input, logic high turns on power switch.
OUT	A1, B1	OUTPUT	Load-switch output; connect a 100 nF ceramic capacitor from OUT to GND as close as possible to the IC is recommended.

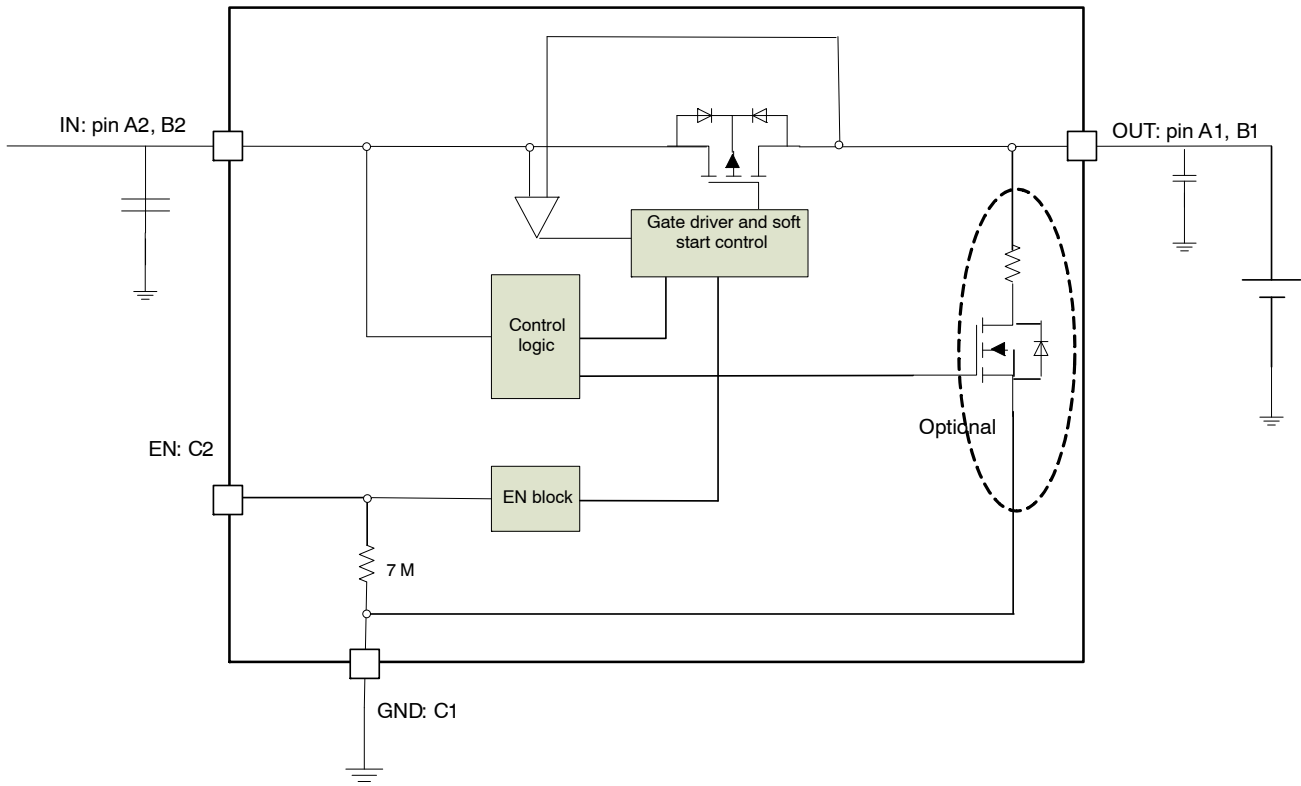


Figure 2. Block Diagram

NCP339

Table 2. MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IN, OUT, EN, Pins: (Note 1)	V_{EN}, V_{IN}, V_{OUT}	-0.3 to +7.0	V
From IN to OUT Pins: Input/Output (Note 1)	V_{IN}, V_{OUT}	-7.0 to +7.0	V
Human Body Model (HBM) ESD Rating are (Note 1 and 2)	ESD HBM	4000	V
Machine Model (MM) ESD Rating are (Note 1 and 2)	ESD MM	250	V
Latch-up protection (Note 3) – Pins IN, OUT, EN	LU	100	mA
Maximum Junction Temperature	T_J	-40 to +125	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C
Moisture Sensitivity (Note 4)	MSL	Level 1	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Table 3. OPERATING CONDITIONS

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IN}	Operational Power Supply		1.2		5.5	V
V_{EN}	Enable Voltage		0		5.5	
T_A	Ambient Temperature Range		-40	25	+85	°C
T_J	Junction Temperature Range		-40	25	+125	°C
C_{IN}	Decoupling input capacitor		1			μF
C_{OUT}	Decoupling output capacitor		100			nF
$R_{\theta JA}$	Thermal Resistance Junction to Air	WLCSP package (Note 3)		100		°C/W
I_{OUT}	Maximum DC current				3	A
P_D	Power Dissipation Rating (Note 4)	$T_A \leq 25\text{ °C}$	WLCSP package		1	W
		$T_A = 85\text{ °C}$	WLCSP package		0.4	W

1. According to JEDEC standard JESD22-A108.

2. Moisture Sensitivity Level (MSL): 1 per IPC/JEDEC standard: J-STD-020.

3. The $R_{\theta JA}$ is dependent of the PCB heat dissipation and thermal via.

4. The maximum power dissipation (P_D) is given by the following formula:

$$P_D = \frac{T_{JMAX} - T_A}{R_{\theta JA}}$$

NCP339

Table 4. ELECTRICAL CHARACTERISTICS

Min & Max Limits apply for T_A between -40°C to $+85^{\circ}\text{C}$ for V_{IN} between 1.2 V to 5.5 V (Unless otherwise noted).
Typical values are referenced to $T_A = +25^{\circ}\text{C}$ and $V_{IN} = 5\text{ V}$ (Unless otherwise noted).

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
POWER SWITCH							
R_{DSON}	Static drain-source on-state resistance	$V_{in} = 5.5\text{ V}$	$I_{out} = 200\text{ mA}$, $T_A = 25^{\circ}\text{C}$		18		$\text{m}\Omega$
		$V_{in} = 5.5\text{ V}$	$T_J = 125^{\circ}\text{C}$			30	
		$V_{in} = 4.5\text{ V}$	$I_{out} = 200\text{ mA}$, $T_A = 25^{\circ}\text{C}$		19		
			$T_J = 125^{\circ}\text{C}$			30	
		$V_{in} = 3.3\text{ V}$	$I_{out} = 200\text{ mA}$, $T_A = 25^{\circ}\text{C}$		22		
			$T_J = 125^{\circ}\text{C}$			30	
		$V_{in} = 2.5\text{ V}$	$I_{out} = 200\text{ mA}$, $T_A = 25^{\circ}\text{C}$		27		
			$T_J = 125^{\circ}\text{C}$			40	
		$V_{in} = 1.8\text{ V}$	$I_{out} = 200\text{ mA}$, $T_A = 25^{\circ}\text{C}$		37		
			$T_J = 125^{\circ}\text{C}$			60	
	$V_{in} = 1.5\text{ V}$	$I_{out} = 200\text{ mA}$, $T_A = 25^{\circ}\text{C}$		48			
		$T_J = 125^{\circ}\text{C}$			110		
R_{dis}	Output discharge path	EN = low	Discharge path option		70	90	Ω
V_{IH}	High-level input voltage			1.2			V
V_{IL}	Low-level input voltage					0.8	
R_{pd}	EN pull down resistor			5.5	7.1	9.5	$\text{M}\Omega$

REVERSE CURRENT BLOCKING

V_{rev_thr}	Reverse threshold	$V_{out} - V_{in}$			40		mV
V_{rev_hyst}	Reverse threshold hysteresis				60		mV
T_{rev}	Reverse comparator response time	$V_{out} - V_{in} > V_{rev_thr}$			2.5		μs

QUIESCENT CURRENT

I_{std}	Standby current	$V_{in} = 4.2\text{ V}$	EN = low, No load, GND current		0.35	0.6	μA
I_{in_leak}	Mos leakage current	$V_{in} = 4.2\text{ V}$	EN = low, $V_{out} = \text{GND}$, V_{out} current		9	200	nA
I_q	Quiescent current	$V_{in} = 4.2\text{ V}$	EN = high, No load, GND current		1.0	1.5	μA
I_{out_leak}	Output leakage current	$V_{out} = 4.2\text{ V}$	$V_{in} = \text{GND}$		16	200	nA

TIMINGS

T_{EN}	Enable time	$V_{in} = 4.2\text{ V}$ (Note 6)	$R_L = 5\ \Omega$, $C_{out} = 100\ \mu\text{F}$		1.7		ms
T_R	Output rise time				2.7		
T_{ON}	ON time ($T_{EN} + T_R$)				4.4		
T_F	Output fall time				1.5		
T_{EN}	Enable time	$V_{in} = 4.2\text{ V}$ (Note 6)	$R_L = 25\ \Omega$, $C_{out} = 1\ \mu\text{F}$	0.5	1.0	2.5	ms
T_R	Output rise time			0.4	1.5	2.3	
T_{ON}	ON time ($T_{EN} + T_R$)			0.9	2.5	4.8	
T_F	Output fall time				0.06	0.1	

5. Guaranteed by design and characterization.

6. Parameters are guaranteed for C_{LOAD} and R_{LOAD} connected to the OUT pin with respect to the ground.

Table 4. ELECTRICAL CHARACTERISTICS

Min & Max Limits apply for T_A between -40°C to $+85^{\circ}\text{C}$ for V_{IN} between 1.2 V to 5.5 V (Unless otherwise noted).
 Typical values are referenced to $T_A = +25^{\circ}\text{C}$ and $V_{IN} = 5\text{ V}$ (Unless otherwise noted).

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
T_{EN}	Enable time	$V_{in} = 4.2\text{ V}$ (Note 6)	$R_L = 150\ \Omega, C_{out} = 100\ \mu\text{F}$		1.7		ms
T_R	Output rise time				1.5		
T_{ON}	ON time ($T_{EN} + T_R$)				3.2		
T_{DIS}	Disable time				1.8		
T_F	Fall time				4		
T_{OFF}	Output fall time ($T_F + T_{DIS}$)				42		

- 5. Guaranteed by design and characterization.
- 6. Parameters are guaranteed for C_{LOAD} and R_{LOAD} connected to the OUT pin with respect to the ground.

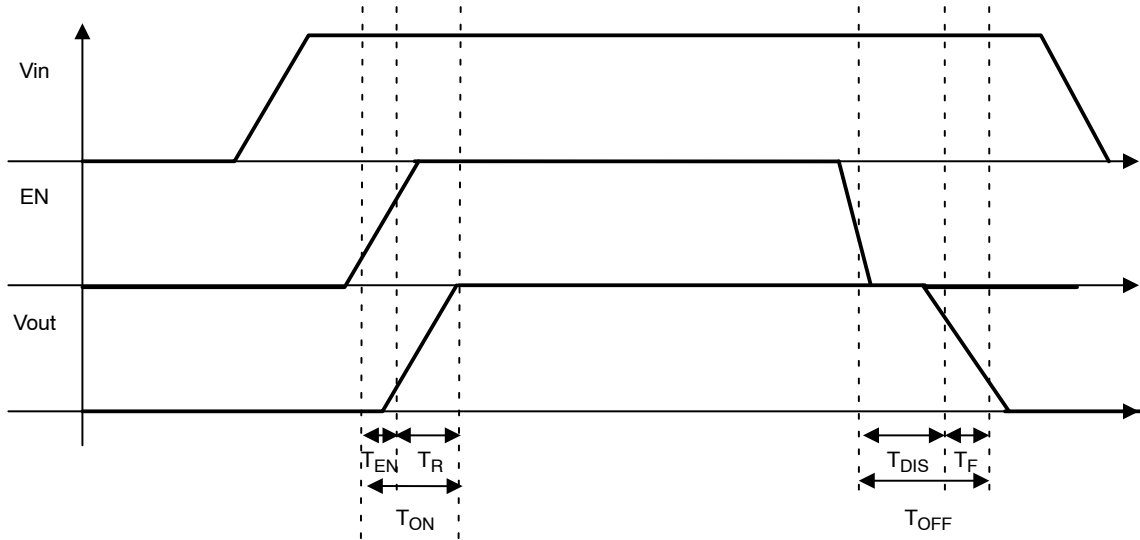


Figure 3. Timings

NCP339

TYPICAL CHARACTERISTICS

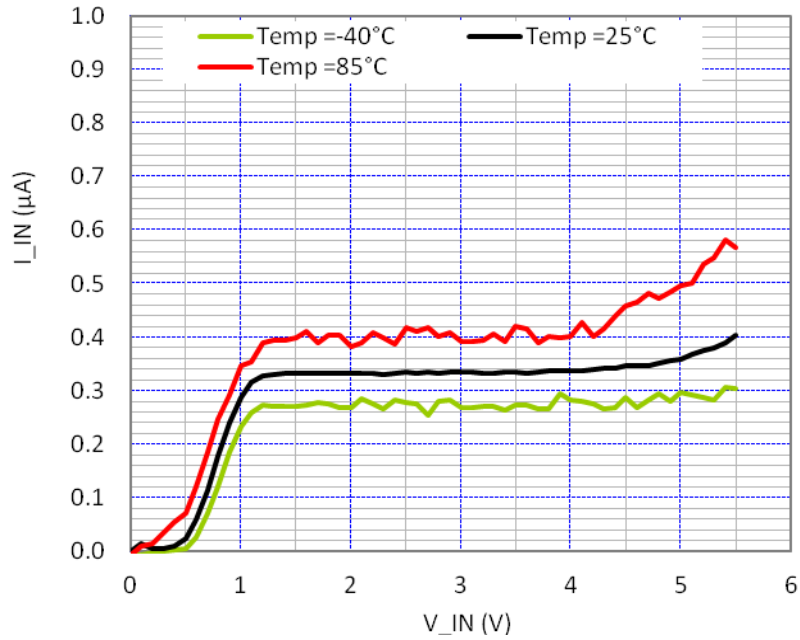


Figure 4. Standby Current (μA) versus V_{in} (V)

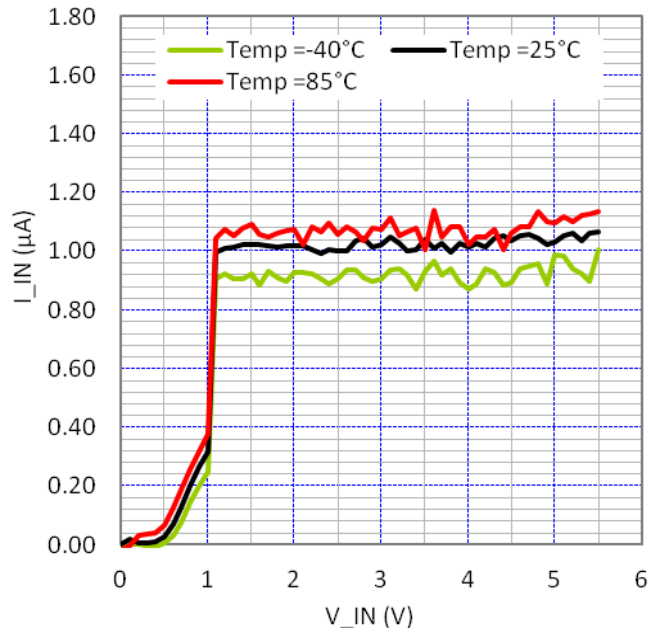


Figure 5. Quiescent Current (μA) versus V_{in} (V)

NCP339

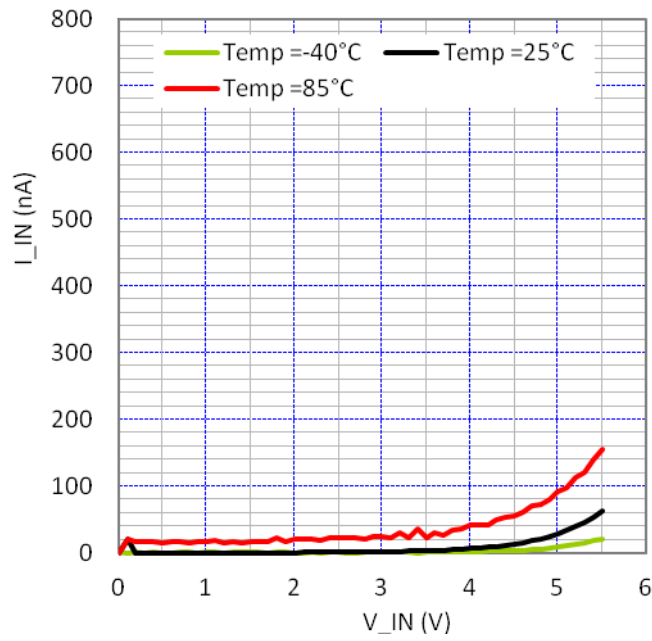


Figure 6. Reverse Current (nA) versus V_{in} (V)

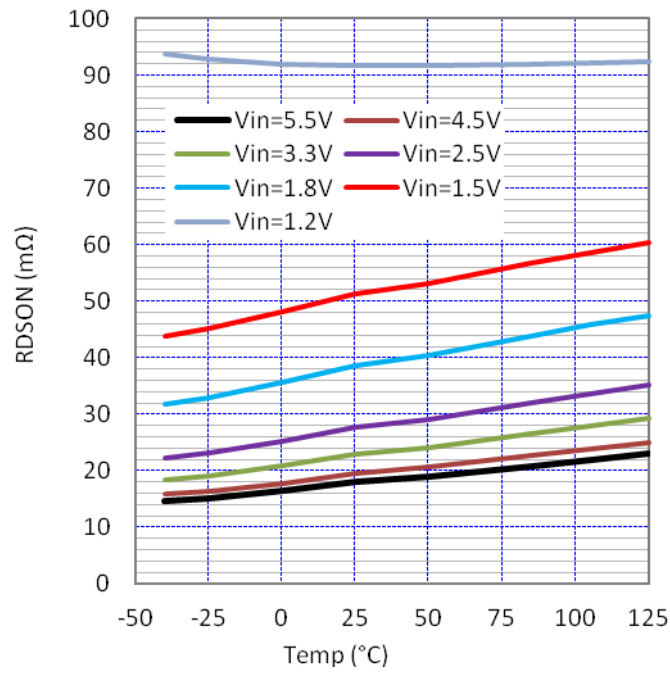


Figure 7. $R_{DS(on)}$ ($m\Omega$) versus Temperature ($I_{LOAD} = 100\text{ mA}$)

NCP339

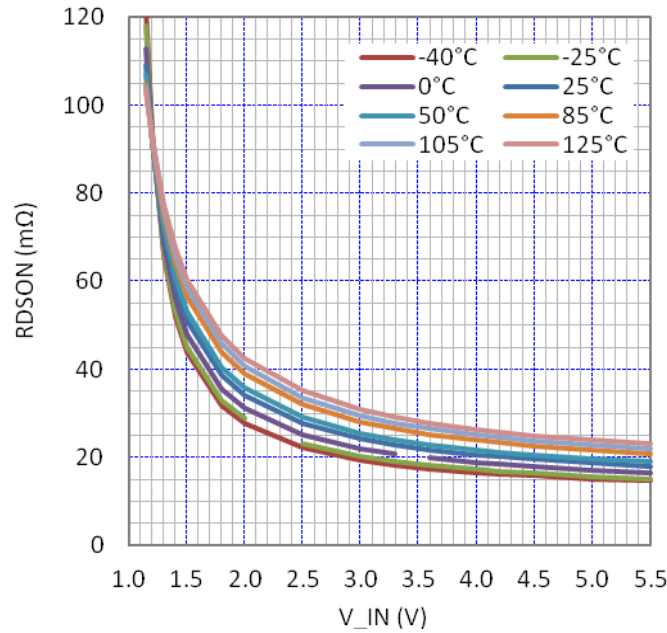


Figure 8. R_{DSON} (mΩ) versus Vin (V)

FUNCTIONAL DESCRIPTION

Overview

The NCP339 is a high side P channel MOSFET power distribution switch designed to isolate ICs connected on the battery in order to save energy. The part can be turned on, with a wide range of battery from 1.2 V to 5.5 V. Reverse blocking from output to input control is embedded in the IC to eliminate leakage current if V_{out} voltage exceed front end power supply.

Enable Input

Enable pin is an active high. The path is opened when EN pin is tied low (disable), forcing P MOS switch off.

The IN/OUT path is activated with a minimum of V_{in} of 1.2 V and EN forced to high level.

Blocking Control

The reverse blocking feature allows to avoid reverse current, through the PMOS fet if a voltage is applied on V_{out} pin, and V_{rev_thr} above the V_{in} pin. This function is available, whatever the EN logic pin state (High or low). To retrieve normal state, V_{in}-V_{out} must be higher to hysteresis of the reverse blocking comparator (V_{rev_hyst}). The reverse blocking comparator response time is set to T_{rev}.

Table 5. CONTROL LOGIC

V _{IN}	V _{OUT}	EN
Present	Mos OFF	Low
Present	Mos ON	High
Mos OFF	V _{OUT} > V _{IN}	x

Auto Discharge (Optional)

NMOS FET is placed between the output pin and GND, in order to discharge the application capacitor connected on OUT pin.

The auto-discharge is activated when EN pin is set to low level (disable state).

The discharge path (Pull down NMOS) stays activated as long as EN pin is set at low level and V_{in} > 1.2 V.

In order to limit the current across the internal discharge Nmosfet, the typical value is set at 70 Ω.

C_{in} and C_{out} Capacitors

C_{in} 1 μF and C_{out} 100 nF , at least, capacitors must be placed as close as possible the part to for stability improvement.

For inrush effects at start up, it's recommended to respect C_{in} > C_{out} size.

APPLICATION INFORMATION

Power Dissipation

Main contributor in term of junction temperature is the power dissipation of the power MOSFET. Assuming this, the power dissipation and the junction temperature in normal mode can be calculated with the following equations:

- $P_D = R_{DS(on)} \times (I_{OUT})^2$
 P_D = Power dissipation (W)
 $R_{DS(on)}$ = Power MOSFET on resistance (Ω)
 I_{OUT} = Output current (A)
- $T_J = P_D \times R_{\theta JA} + T_A$
 T_J = Junction temperature ($^{\circ}C$)
 $R_{\theta JA}$ = Package thermal resistance ($^{\circ}C/W$)
 T_A = Ambient temperature ($^{\circ}C$)

PCB Recommendations

The NCP339 integrates an up to 3 A rated PMOS FET, and the PCB design rules must be respected to properly evacuate the heat out of the silicon. By increasing PCB area, especially around IN and OUT pins, the $R_{\theta JA}$ of the package can be decreased, allowing higher power dissipation.

Routing example: 2 oz, 4 layers with vias across 2 internal inners.

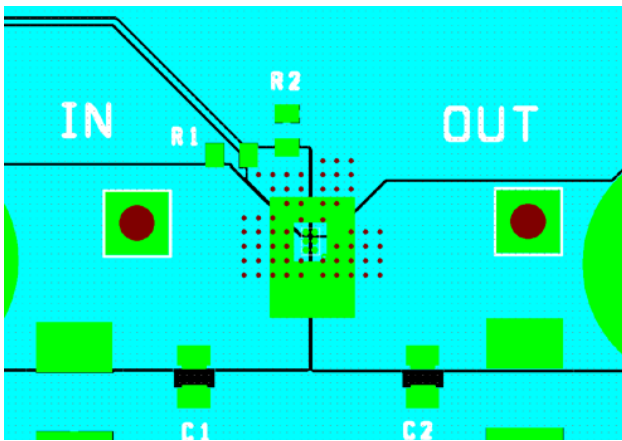


Figure 9.

Example of application definition.

$$T_J - T_A = R_{\theta JA} \times P_D = R_{\theta JA} \times R_{DS(on)} \times I^2$$

T_J : junction temperature.

T_A : ambient temperature.

R_{θ} = Thermal resistance between IC and air, through PCB.

$R_{DS(on)}$: intrinsic resistance of the IC Mosfet.

I : load DC current.

Taking into account of R_{θ} obtain with:

- 1 oz, 2 layers: $100^{\circ}C/W$.
 At 3 A, $25^{\circ}C$ ambient temperature, $R_{DS(on)}$ 20 m Ω @
 V_{in} 5 V, the junction temperature will be:
 $T_J = T_A + R_{\theta} \times P_D = 25 + (0.02 \times 3^2) \times 100 = 43^{\circ}C$

Taking into account of R_{θ} obtain with:

- 2 oz, 4 layers: $60^{\circ}C/W$.
 At 3 A, $65^{\circ}C$ ambient temperature, $R_{DS(on)}$ 24 m Ω @
 V_{in} 5 V, the junction temperature will be:
 $T_J = T_A + R_{\theta} \times P_D = 65 + (0.024 \times 3^2) \times 60 = 78^{\circ}C$

ORDERING INFORMATION

Device	Marking	Option	Package	Shipping†
NCP339AFCT2G	NP	Without Auto-discharge	WLCSP6, 1 x 1.5 mm (Pb-Free)	3000 / Tape & Reel
NCP339BFCT2G	DP	With Auto-discharge	WLCSP6, 1 x 1.5 mm (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

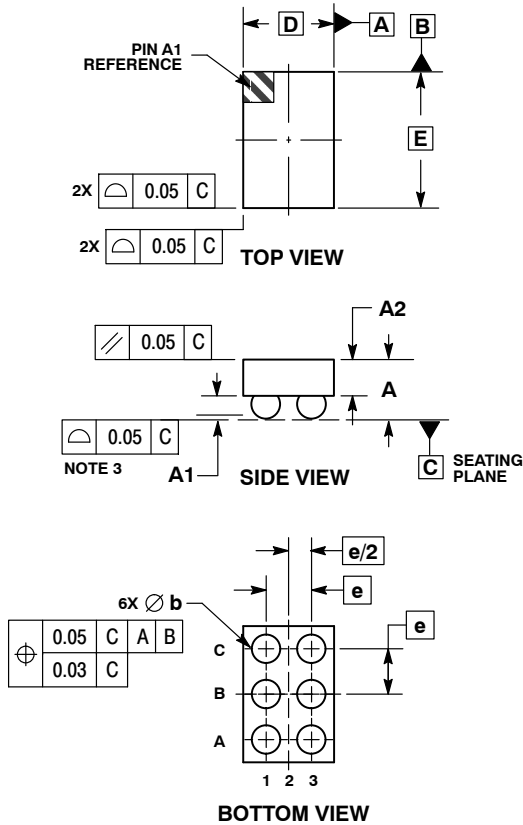
ON Semiconductor®



SCALE 4:1

WLCSP6, 1.00x1.50
CASE 567FH
ISSUE O

DATE 17 APR 2012

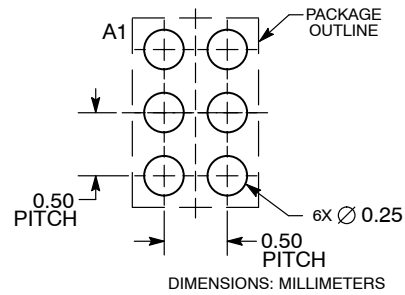


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. COPLANARITY APPLIES TO SPHERICAL CROWNS OF SOLDER BALLS.

DIM	MILLIMETERS	
	MIN	MAX
A	0.54	0.63
A1	0.22	0.28
A2	0.33 REF	
b	0.29	0.34
D	1.00 BSC	
E	1.50 BSC	
e	0.50 BSC	

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON79918E	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	WLCSP6, 1.00X1.50	PAGE 1 OF 1

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.